


EE-SB5M/SB5MC/SB5V/SB5VC/SB5V-E

Photomicrosensor with 80-mA
Switching Capacity that can be Built into
Equipment

- Built-in amplifier with NPN output
- Models available with 5- to 12-VDC and 5- to 15-VDC input
- CMOS- and TTL-compatible
- 19-mm sensing distance (EE-SB5V-E)
- Model with easy adjustment with an external sensitivity adjuster (EE-SB5V)
- Connectors available (EE-1001/1006)
- Convert to PNP output with EE-2002 conversion connector



Ordering Information

Appearance	Sensing method	Sensing distance	Output configuration	Weight	Part number
	Diffuse	5 mm	Light-ON	Approx. 3.0 g	EE-SB5M
			Dark-ON		EE-SB5MC
			Light-ON		EE-SB5V
			Dark-ON		EE-SB5VC
		19 mm	Light-ON	Approx. 2.8 g	EE-SB5V-E

■ ACCESSORIES

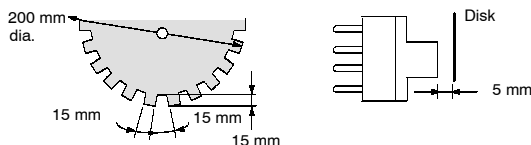
Name	Part number
Solder connector	EE-1001
Connector with 2 m cable	EE-1006

Specifications

■ RATINGS

Item	Diffuse				
	EE-SB5M	EE-SB5MC	EE-SB5V(-E)	EE-SB5VC	
Supply voltage	5 to 12 VDC ±10%, ripple (p-p): 10% max.		5 to 15 VDC ±10%, ripple (p-p): 10% max.		
Current consumption	36 mA max.		48 mA max. (DC current: I _F = 25 mA)		
Maximum forward direct current (I _F)	—		30 mA max.		
Forward voltage (V _F)	—		1.5 V max. (I _F = 30 mA)		
Reverse voltage (V _R)	—		4 V max.		
Standard reference object	White paper with reflection factor of 90% (standard sensing object: 15 x 15 mm)				
Differential distance	0.1 mm				
Control output	At 5 to 24 VDC: 80-mA load current (I _C) with a residual voltage of 0.8 V max. When driving TTL: 40-mA load current (I _C) with a residual voltage of 0.4 V max.				
Output configuration	Transistor on output stage without detecting object	OFF	ON	OFF	ON
	Transistor on output stage with detecting object	ON	OFF	ON	OFF
Response frequency (See note)	50 Hz				
Connecting method	EE-1001/1006 Connectors; soldering terminals/cordset				
Light source	GaAs infrared LED with a peak wavelength of 940 nm				
Receiver	Si photo-transistor with a sensing wavelength of 850 nm max.				

Note: The response frequency was measured by detecting the following disks rotating.

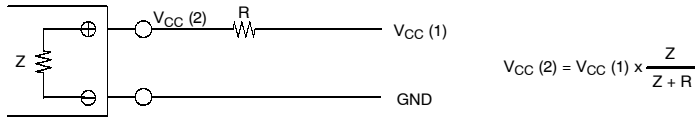


■ CHARACTERISTICS

Ambient temperature	Operating	-25°C to 55°C (-13°F to 131°F)
	Storage	-30°C to 80°C (-22°F to 176°F)
Ambient humidity	Operating	45% to 85%
	Storage	35% to 95%
Vibration resistance	Destruction: 20 to 2,000 Hz (with a peak acceleration of 20G's), 1.5-mm double amplitude for 4 min each in X, Y, and Z directions	
Shock resistance	Destruction: 500 m/s ² for 3 times each in X, Y, and Z directions	
Soldering heat resistance	260°±5°C (See Note.) when the portion between the tip of the terminals and the position 1.5 mm from the terminal base is dipped into the solder for 10±1 seconds	

Note: This conforms to MIL-STD-750-2031-1.

Note: Supply 5 to 12 V to the EE-SB5M(C). Wire as shown by the following diagram if the supply voltage exceeds 12 V.



Note: Z is the internal impedance between the positive and negative terminals.

Model	V _{CC} (2)	Z (Ω)
EE-SB5M(C)	5 to 12 V	360

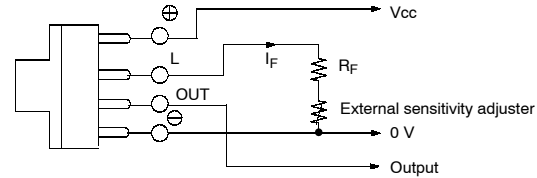
Precautions

Refer to the Technical Information Section for general precautions.

An external sensitivity adjuster can be connected to the EE-SB5V(C), EE-SB5V-E Photomicrosensor. When connecting the sensitivity adjuster, insert resistor R_F (current-limiting resistor), as shown by the diagram. The value of R_F is obtainable as follows:

$$R_F > (V_{CC} - 1.5 \text{ V})/30 \text{ mA}$$

Note: The EE-SB5V(C) and EE-SB5V-E have no constant current circuit to protect the LED. For this reason, the LED will be damaged by excessive current applied to the positive terminal. To prevent potential LED damage, connect a current-limiting resistor, as shown previously.



NOTE: DIMENSIONS SHOWN ARE IN MILLIMETERS. To convert millimeters to inches divide by 25.4.

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